Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Previously Presented) A thin-film transistor, comprising:

an active region;

a source region; and

a drain region, the source region and the drain region being provided at each side of the active region, respectively;

an area of a cross section of the source region being approximately equal to an area of a cross section of the drain region, said cross sections taken along a plane generally perpendicular to a mounting surface of the thin-film transistor;

the source region and the drain region including regions adjacent to the active region, the adjacent regions including lightly doped impurity regions with an impurity concentration less than an impurity concentration of the drain region; and

the lightly doped impurity regions being provided in an asymmetrical form in which the lightly doped impurity region in the source region is smaller than the lightly doped impurity region in the drain region.

2. (Original) The thin-film transistor according to claim 1, the length, in the longitudinal direction of a channel, of the lightly doped impurity region in the drain region being longer than the lightly doped impurity region in the source region.

3. (Canceled).

4. (Original) The thin-film transistor according to claim 1, further including a gate electrode provided at a position facing the active region, with an insulating layer provided therebetween,

the boundary between each lightly doped impurity region and the active region approximately matching one end of the gate electrode.

5.-17. (Canceled).